

AMENDMENTS TO THE SPECIFICATION

Please amend the first full paragraph on page 7 as follows:

Suppose that the left side of FIG. 4(b) is closer to the center (inward) of the wafer 101. In that case, if the antireflection film 105 and the silicon nitride film 104 [[105]] are dry-etched using the resist pattern 108 as a mask, a first deposit 107A deposited on an inward side face of the resist pattern 108 is adhered more thickly than a second deposit 107B deposited on an outward side face of the resist pattern 108. It should be noted that the amounts of adherence of the deposits are inevitably out of balance in the pattern in which distances (spaces) each located between lines adjacent to each other are out of balance.

Please amend the last paragraph on page 7 as follows:

Next, as shown in FIG. 5(b), the antireflection film 105 and the silicon nitride film 104 [[105]] are dry-etched under the condition such as the etching condition D shown in FIG. 1, for example, so that sidewall deposits are considerably increased. In this manner, the amount of the second deposit 107B deposited on an outward side face of the resist pattern 108 is also increased.

Please amend the fourth paragraph on page 8 as follows:

Next, as shown in FIG. 6(b), the antireflection film 105 and the silicon nitride film 104 [[105]] are dry-etched under the condition such as the etching condition B or E shown in FIG. 1, for example, so that almost no sidewall deposits are adhered. Therefore, in this case, an imbalanced adhesion of the deposits to both sidewalls of the resist pattern 108 does not occur.

Please amend the second paragraph on page 9 as follows:

It should be noted that since an imbalanced deposition of the sidewall deposits on both side faces of the resist pattern 108 [[101]], which are parallel to a radial direction of the wafer 101, does not occur in the first place, and thus no problem is caused.

Please amend the last paragraph on page 15 as follows:

Next, as shown in FIG. 8(b), the exposed resist film 16A is developed to provide a resist pattern 16. In this embodiment, each cross section of the resist pattern 16 [[16A]] shown is extending perpendicularly to a radial direction of the wafer 11.

Please amend the second paragraph on page 18 as follows:

Next, as shown in FIG. 9(b), the exposed resist film 16A is developed to provide a resist pattern 16. Also in this embodiment, each cross section of the resist pattern 16 [[16A]] shown is extending perpendicularly to a radial direction of the wafer 11.

Please amend the first full paragraph on page 21as follows:

Next, as shown in FIG. 10(b), the exposed resist film 16A is developed to provide a resist pattern 16. Also in this embodiment, each cross section of the resist pattern 16 [[16A]] shown is extending perpendicularly to a radial direction of the wafer 11.

Please amend the third paragraph on page 22 as follows:

By employing this etching condition, a first deposit **17A** [[107A]] deposited on an inward side face of the resist pattern **16** and a second deposit **17B** deposited on an outward side face of the resist pattern **16** are both relatively thickly adhered as shown in FIG. 10(c).